

200MHz, High Speed, CMOS, Rail-to-Rail Operational Amplifier

Advanced

1. Features

- Single-Supply Operation from +2.5V ~ +5.5V
- Rail-to-Rail Input / Output
- Gain-Bandwidth Product: 200MHz (Typ.)
- Low Input Bias Current: 10pA (Typ.)

- Low Offset Voltage: 10mV (Max.)
- Quiescent Current:7.8mA (Typ.)
- Operating Temperature: -40°C ~ +125°C
- Available in MSOP8 and SOP8 Packages

2. General Description

The GT7112 is wideband, low-noise, low-distortion operational amplifier, that offer rail-to-rail output and single-supply operation down to 2.5V. They draw 7.8mA of quiescent supply current, as well as low input voltage-noise density $(13nV/\sqrt{Hz})$ and low input current-noise density $(400fA/\sqrt{Hz})$. These features make the devices an ideal choice for applications that require low distortion and low noise. The GT7112 has output which swing rail-to-rail and their input common-mode voltage range includes ground and offer wide bandwidth to 200MHz (G=+1) . They are specified over the extended industrial temperature range $(-45^{\circ}\text{C} \sim 125^{\circ}\text{C})$. The single GT7112 is available in space-saving, MSOP8 and SOP-8 packages.

3. Applications

- Portable Equipment
- Mobile Communications
- Smoke Detector
- Sensor Interface

- Medical Instrumentation
- Handheld Test Equipment
- Imaging/video

4. Pin Configuration

4.1 GT7112 MSOP8 and SOP8 (Top View)

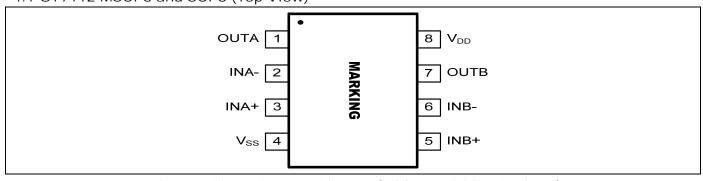


Figure 1. Pin Assignment Diagram (MSOP8 and SOP8 Package)

Note: Please see section "Part Markings" for detailed Marking Information.

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5. Application Information

5.1 Size

GT7112 series op amps are unity-gain stable and suitable for a wide range of general-purpose applications. The small footprints of the GT7112 series packages save space on printed circuit boards and enable the design of smaller electronic products.

5.2 Power Supply Bypassing and Board Layout

GT7112 series operates from a single 2.5V to 5.5V supply or dual ± 1.25 V to ± 2.75 V supplies. For best performance, a 0.1μ F ceramic capacitor should be placed close to the V_{DD} pin in single supply operation. For dual supply operation, both V_{DD} and V_{SS} supplies should be bypassed to ground with separate 0.1μ F ceramic capacitors.

5.3 Low Supply Current

The low supply current (typical 7.8mA) of GT7112 series will help to maximize battery life. They are ideal for battery powered systems

5.4 Operating Voltage

GT7112 series operate under wide input supply voltage (2.2V to 5.5V). In addition, all temperature specifications apply from -40 °C to +125 °C. Most behavior remains unchanged throughout the full operating voltage range. These guarantees ensure operation throughout the single Li-lon battery lifetime

5.5 Rail-to-Rail Input

The input common-mode range of GT7112 series extends 100mV beyond the supply rails (V_{SS} -0.1V to V_{DD} +0.1V). This is achieved by using complementary input stage. For normal operation, inputs should be limited to this range.

5.6 Rail-to-Rail Output

Rail-to-Rail output swing provides maximum possible dynamic range at the output. This is particularly important when operating in low supply voltages. The output voltage of GT7112 series can typically swing to less than 10mV from supply rail in light resistive loads (>100k Ω), and 60mV of supply rail in moderate resistive loads (10k Ω).

5.7 Capacitive Load Tolerance

The GT7112 series can directly drive 200pF capacitive load in unity-gain without oscillation. Increasing the gain enhances the amplifier's ability to drive greater capacitive loads. In unity-gain configurations, the capacitive load drive can be improved by inserting an isolation resistor $R_{\rm ISO}$ in series with the capacitive load, as shown in *Figure 2*.

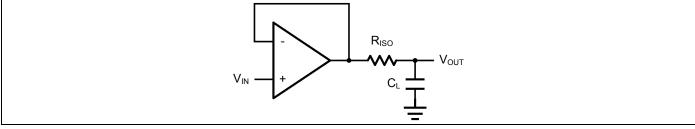


Figure 2. Indirectly Driving a Capacitive Load Using Isolation Resistor

The bigger the R_{ISO} resistor value, the more stable V_{OUT} will be. However, if there is a resistive load R_L in parallel with the capacitive load, a voltage divider (proportional to R_{ISO}/R_L) is formed, this will result in a gain error.

The circuit in *Figure 3* is an improvement to the one in *Figure 2*. R_F provides the DC accuracy by feed-forward the V_{IN} to R_L . C_F and R_{ISO} serve to counteract the loss of phase margin by feeding the high frequency component of the output signal back to the amplifier's inverting input, thereby preserving the phase margin in the overall feedback loop. Capacitive drive can be increased





by increasing the value of C_F. This in turn will slow down the pulse response.

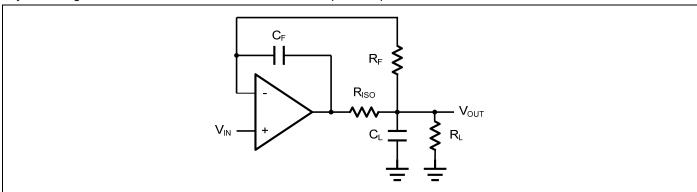


Figure 3. Indirectly Driving a Capacitive Load with DC Accuracy

5.8 Differential amplifier

The differential amplifier allows the subtraction of two input voltages or cancellation of a signal common the two inputs. It is useful as a computational amplifier in making a differential to single-end conversion or in rejecting a common mode signal. *Figure 4.* shown the differential amplifier using GT7112.

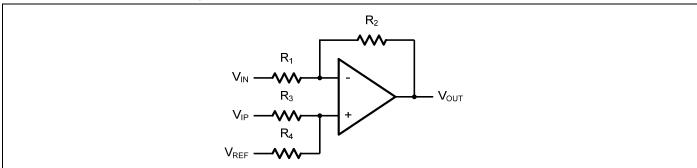


Figure 4. Differential Amplifier

$$V_{\text{OUT}} = (\frac{R_1 + R_2}{R_3 + R_4}) \frac{R_4}{R_1} V_{\text{IN}} - \frac{R_2}{R_1} V_{\text{IP}} + (\frac{R_1 + R_2}{R_3 + R_4}) \frac{R_3}{R_1} V_{\text{REF}}$$

If the resistor ratios are equal (i.e. R₁=R₃ and R₂=R₄), then

$$V_{\text{OUT}} = \frac{R_2}{R_1} (V_{\text{IP}} - V_{\text{IN}}) + V_{\text{REF}}$$

5.9 Instrumentation Amplifier

The input impedance of the previous differential amplifier is set by the resistors R_1 , R_2 , R_3 , and R_4 . To maintain the high input impedance, one can use a voltage follower in front of each input as shown in the following two instrumentation amplifiers.

5.10 Three-Op-Amp Instrumentation Amplifier

The triple GT7112 can be used to build a three-op-amp instrumentation amplifier as shown in Figure 5.



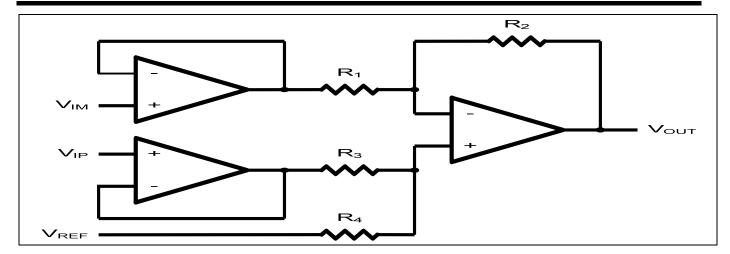


Figure 5. Instrument Amplifier

The amplifier in Figure 5 is a high input impedance differential amplifier with gain of R_2/R_1 . The two differential voltage followers assure the high input impedance of the amplifier.

5.11Two-Op-Amp Instrumentation Amplifier

GT7112 can also be used to make a high input impedance two-op-amp instrumentation amplifier as shown in Figure 6.

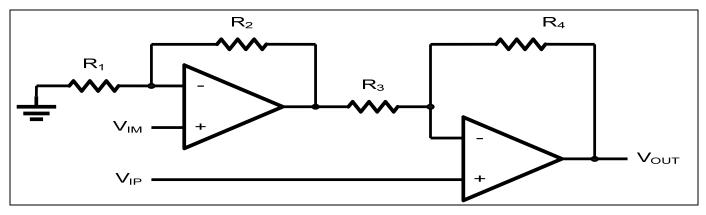


Figure 6. Instrument Amplifier

$$V_o = (1 + \frac{R_4}{R_3})(V_2 - V_1)$$

Where R_1 = R_3 and R_2 = R_4 . If all resistors are equal, then V_0 = $2(V_2$ - $V_1)$

5.12 Single-Supply Inverting Amplifier

The inverting amplifier is shown in Figure 6. The capacitor C_1 is used to block the DC signal going into the AC signal source V_{IN} . The value of R_1 and C_1 set the cut-off frequency to $f_C=1/(2\pi R_1C_1)$. The DC gain is defined by $V_{OUT}=-(R_2/R_1)V_{IN}$



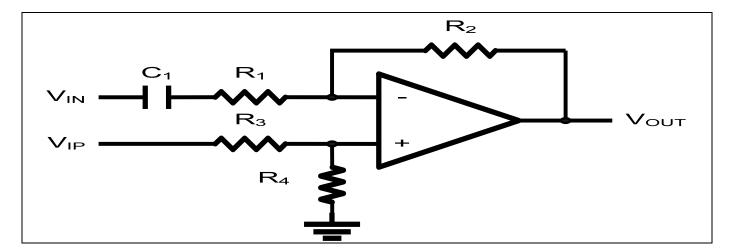


Figure 7. Instrument Amplifier

5.13 Low Pass Active Filter

The low pass active filter is shown in *Figure 8*. The DC gain is defined by $-R_2/R_1$. The filter has a -20dB/decade roll-off after its corner frequency $f_C=1/(2\pi R_3 C_1)$.

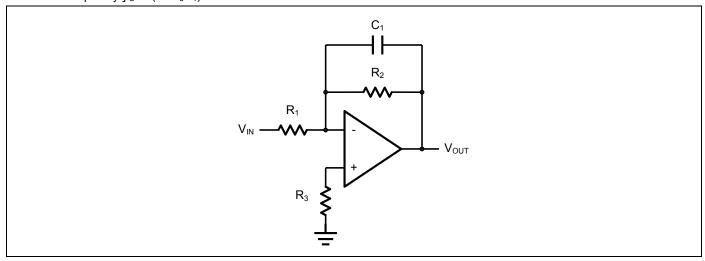


Figure 8. Low Pass Active Filter

5.14 Sallen-Key 2nd Order Active Low-Pass Filter

GT7112 can be used to form a 2^{nd} order Sallen-Key active low-pass filter as shown in *Figure 9*. The transfer function from V_{IN} to V_{OUT} is given by

$$\frac{V_{OUT}}{V_{IN}}(S) = \frac{\frac{1}{C_1 C_2 R_1 R_2} A_{LP}}{S^2 + S(\frac{1}{C_1 R_1} + \frac{1}{C_1 R_2} + \frac{1}{C_2 R_2} - \frac{A_{LP}}{C_2 R_2}) + \frac{1}{C_1 C_2 R_1 R_2}}$$

Where the DC gain is defined by A_{LP}=1+R₃/R₄, and the corner frequency is given by



$$\mathcal{O}C = \sqrt{\frac{1}{C_1 C_2 R_1 R_2}}$$

The pole quality factor is given by

$$\frac{\omega C}{Q} = \frac{1}{C_1 R_1} + \frac{1}{C_1 R_2} + \frac{1}{C_2 R_2} - \frac{A_{LP}}{C_2 R_2}$$

Let R1=R2=R and C1=C2=C, the corner frequency and the pole quality factor can be simplified as below

$$\omega_C = \frac{1}{CR}$$

And $Q=2-R_3/R_4$

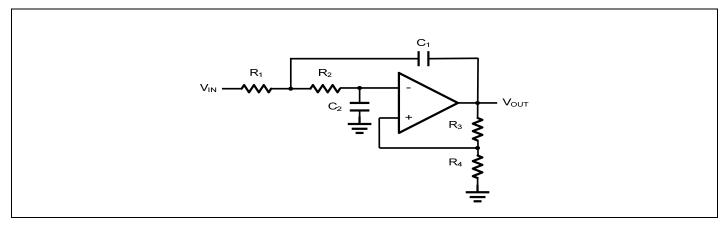


Figure 9. Sanllen-Key 2nd Order Active Low-Pass Filter

5.15 Sallen-Key 2nd Order high-Pass Active Filter

The 2^{nd} order Sallen-key high-pass filter can be built by simply interchanging those frequency selective components R_1 , R_2 , C_1 , and C_2 as shown in *Figure 10*.

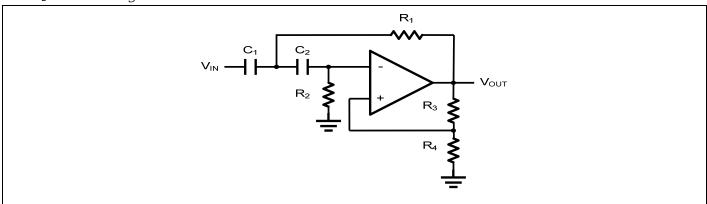


Figure 10. Sanllen-Key 2nd Order Active High-Pass Filter

$$\frac{V_{OUT}}{V_{IN}}(S) = \frac{S^2 A_{HP}}{S^2 + S(\frac{1}{C_1 R_1} + \frac{1}{C_2 R_2} + \frac{1 - A_{HP}}{C_1 R_1}) + \frac{1}{C_1 C_2 R_1 R_2}}$$

Where A_{HP}=1+R₃/R₄



6. Electrical Characteristics

6.1 Absolute Maximum Ratings

Condition	Min	Max		
Power Supply Voltage (V _{DD} to Vss)	-0.5V	+7V		
Analog Input Voltage (IN+ or IN-)	Vss-0.5V	V _{DD} +0.5V		
PDB Input Voltage	Vss-0.5V +7V			
Operating Temperature Range	-40°C	+125°C		
Junction Temperature	+150°C			
Storage Temperature Range	-65°C +150°C			
Lead Temperature (soldering, 10sec)	+300°C			
Package Thermal Resistance (T _A =+25°C)				
MSOP8, θ _{JA}	190°C			
SOP8, θ _{JA}	130°C			

Note: Stress greater than those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.



6.2 Electrical Characteristics

 $(V_{DD}=+5V,~Vss=0V,~V_{CM}=0V,~V_{OUT}=V_{DD}/2,~R_L=100K~tied~to~V_{DD}/2,~SHDNB=V_{DD},~T_A=-40^{\circ}C~to~+125^{\circ}C,~unless~otherwise~noted.$ Typical values are at $T_A=+25^{\circ}C.)$ (Notes 1,2)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Supply-Voltage Range		Guaranteed by the PSRR test	2.5	-	5.5	V
Quiescent Supply Current (per Amplifier)	V_{DD}	V _{DD} = 5V	3.1	3.9	4.7	mA
		T _A =25°C	-	±3	±5	
Input Offset Voltage	Vos	T _A =-40°C~+85°C	-	-	±8	mV
		T _A =-40°C~+125°C	-	-	±10	
Input Offset Voltage Tempco	ΔV _{OS} /ΔΤ		-	±2	-	μV/°C
Input Bias Current	Ι _Β	(Note 3)	-	±10	±100	рА
Input Offset Current	Ios	(Note 3)	-	±10	±100	pА
Input Common-Mode Voltage Range	V _{CM}	Guaranteed by the $T_A = 25^{\circ}C$ CMRR test, $T_A = -40^{\circ}C \sim +125^{\circ}C$	-0.1	-	V _{DD} +0.1	V
		$Vss-0.1V \le V_{CM} \le V_{DD} + 0.1V$ $T_A = 25^{\circ}C$	-	75	-	
Common-Mode Rejection Ratio	CMRR	$Vss \le V_{CM} \le 5V_{DD}$ $T_A = 25^{\circ}C$	72	90	-	dB
		Vss-0.1V \leq V _{CM} \leq V _{DD} +0.1V T _A = -40°C ~ +125°C	-	68	-	
Power-Supply Rejection Ratio	PSRR	V _{DD} = +2.5V to +5.5V	75	90	-	dB
		R_L = 10k Ω to $V_{DD}/2$ V_{OUT} = 100mV to V_{DD} -125mV	90	100	-	
Open-Loop Voltage Gain	A _V	R_L = 1k Ω to $V_{DD}/2$ V_{OUT} = 200mV to V_{DD} -250mV	80	95	-	dB
		R_L = 500 Ω to $V_{DD}/2$ V_{OUT} = 350mV to V_{DD} -500mV	70	80	-	
Output Voltage Swing	V _{OUT}	$ V_{IN+}-V_{IN-} \ge 10 \text{mV}$ $V_{DD}-V_{OH}$	-	10	35	
		$R_L = 10k\Omega$ to $V_{DD}/2$ $V_{OL}-V_{SS}$	-	10	30	
		$ V_{IN+}-V_{IN-} \ge 10 \text{mV}$ $V_{DD}-V_{OH}$	-	80	50	>/
		$R_L = 1k\Omega$ to $V_{DD}/2$ $V_{OL}-V_{SS}$	-	30	50	mV
		$ V_{IN+}-V_{IN-} \ge 10 mV$ $V_{DD}-V_{OH}$	-	100	140	
		$R_L = 500\Omega$ to $V_{DD}/2$ $V_{OL}-V_{SS}$	-	100	140	
Output Short-Circuit Current	I _{SC}	Sinking or Sourcing	-	±120	-	mA
-3 dB Gain Bandwidth Product	GBW	$A_V = +1V/V$	-	200	-	MHz
Slew Rate	SR	$A_V = +1V/V$	-	100	-	V/µs



Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Input Capacitance	Cin			1.5		pF
Differential Phase error (NTSC)	DP	G=2,R _L =150Ω	-	0.03	-	Deg
Differential Gain error (NTSC)	DG	G=2,R _L =150Ω	-	0.09	-	dB
Settling Time	ts	To 0.01%, $V_{OUT} = 2V$ step $A_V = +1V/V$	-	52	-	Ns
Capacitive-Load Stability	Cload	No sustained oscillations Av=+1V/V		200		pF
Over Load Recovery Time		V _{IN} × Gain=V _S	-	2	-	μs
Input Voltage Noise Density	e _n	f = 1KHz f=30KHz	-	15 13	-	nV/√Hz
Input Current Noise Density	İn	F=1KHz	-	400		fA/√Hz
Total Harmonic Distortion plus Noise	THD+N	f_{C} =5MHZ,V _{OUT} =2Vp-p,G=+2	-	-60	-	dB

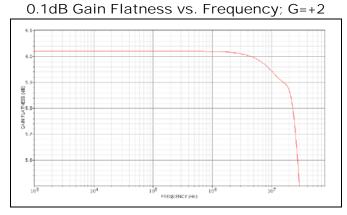
Note 1: All devices are 100% production tested at T_A = +25°C; all specifications over the automotive temperature range is guaranteed by design, not production tested.

Note 2: Parameter is guaranteed by design.

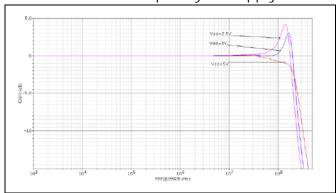
Note 3: Peak-to-peak input noise voltage is defined as six times rms value of input noise voltage.



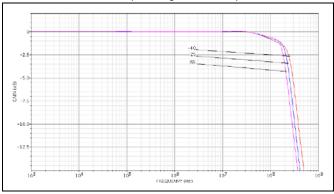
6.3 Typical characteristics



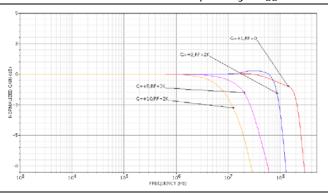
Gain vs. Frequency vs Supply



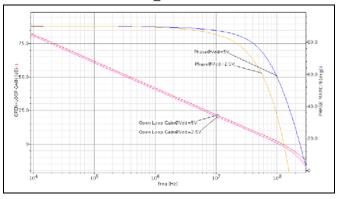
Gain vs. Frequency vs Temperature



Normalized Gain vs. Frequency; $V_{DD}=5V$

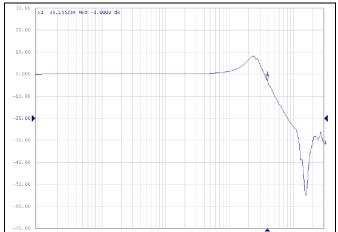


STB_RL=2K

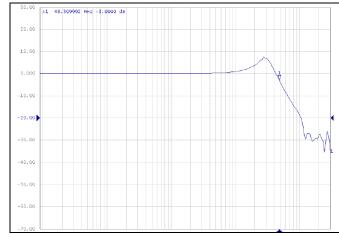




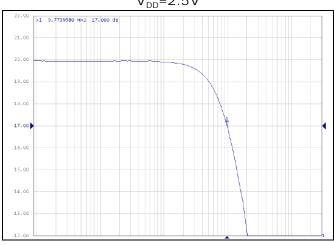




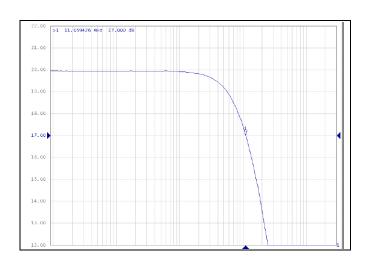
G=+1; RF=2K; $V_{pp}=0.2V$; $V_{DD}=5V$



G=+2;RF=100 Ω ; RI=150 Ω V_{PP}=0.2V; V_{DD}=2.5V



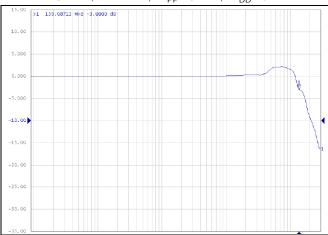
G=-10; RF=2K; $V_{PP}=0.2V$; $V_{DD}=5V$



G=+1; RF=2K; $V_{PP}=0.2V$; $V_{DD}=2.5V$

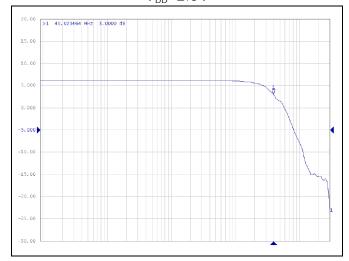


G=+1; RF=2K; $V_{PP}=0.2V$; $V_{DD}=5V$

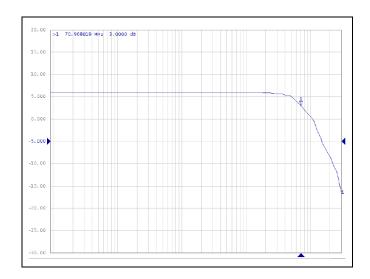




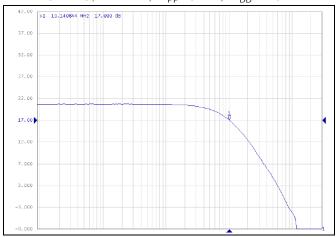
G=+2; RF=100 Ω ; RI=150 Ω V_{pp}=0.2V; V_{DD}=2.5V



G=+2; RF=100 Ω ; RI=150 Ω V_{PP}=0.2V; V_{DD}=5V



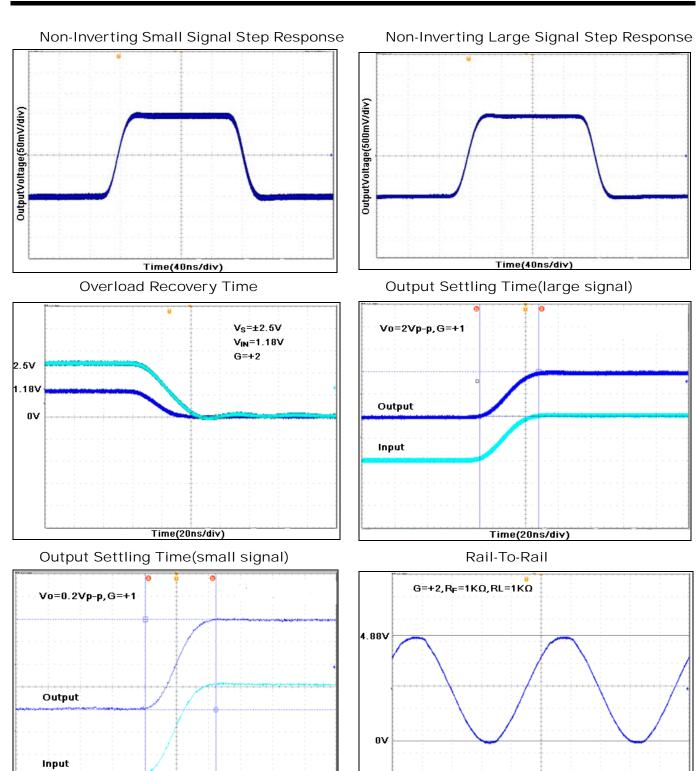
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 $G=+10;RF=2K;V_{PP}=0.2V;V_{DD}=5V$





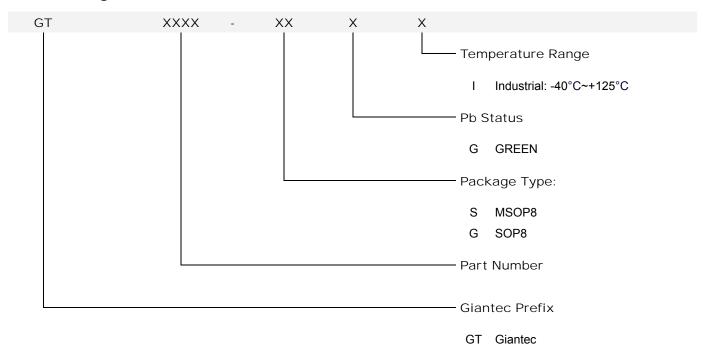


Time(20ns/div)

Time(200ns/div)



7. Ordering Information



Order Number	Package Description	Package Option
GT7112-SGI-TR	MSOP8	Tape and Reel 3000
GT7112-GGI-TR	SOP8	Tape and Reel 4000



8. Part Markings

8.1 GT7112-SGI (Top View)

<u>G</u> <u>T</u>	7			_1_	<u>S</u>	<u>G</u>	
			Lot <u>Num</u> ber				
•	Y	Y	W	W	S	V	

GT7112SGI

Lot Number States the last 9 characters of the wafer lot information

Pin 1 Indicator

YY Seal Year

00 = 2000

01 = 2001

99 = 2099

WW Seal Week

01 = Week 1

02 = Week 2

.

51 = Week 51

52 = Week 52

Subcon Code

J = ASESH

L = ASEKS

/ Die Version

S



8.2 GT7112-GGI (Top View)

<u>G</u>	<u>T</u>		1		1	G	<u>G</u>	1
	_	_	-	Lot Number	_	_	-	
•		<u>Y</u>	<u>Y</u>			<u>S</u>	<u></u>	

GT7112GGI

WW

S

Lot Number States the last 9 characters of the wafer lot information

Pin 1 IndicatorYYSeal Year00 = 2000

01 = 2001 99 = 2099 Seal Week

01 = Week 1 02 = Week 2

.

51 = Week 51 52 = Week 52 Subcon Code J = ASESH

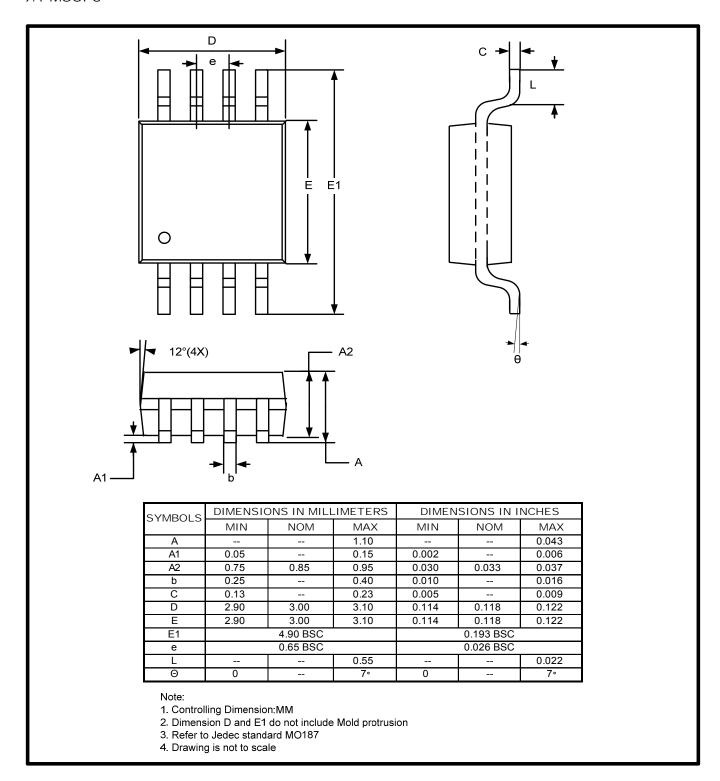
L = ASEKS

Die Version



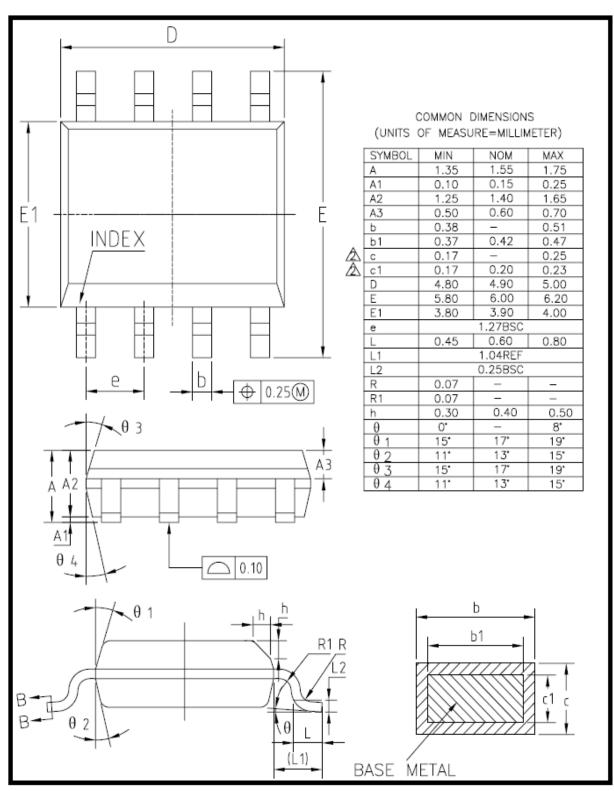
9. Package Information

9.1 MSOP8





9.2 SOP8





10. Revision History

Revision	Date	Descriptions
A0	Sept.,2013	Initial Version